

Yerassimos Panayiotatos

List of Publications by Year in descending order

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61
papers

1,353
citations

288859

22
h-index

356229

35
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61
all docs

61
docs citations

61
times ranked

1321
citing authors

#	ARTICLE	IF	CITATIONS
1	Electrical properties of La ₂ O ₃ and HfO ₂ •La ₂ O ₃ gate dielectrics for germanium metal-oxide-semiconductor devices. Journal of Applied Physics, 2008, 103, .	2.3	109
2	Interface engineering for Ge metal-oxide-semiconductor devices. Thin Solid Films, 2007, 515, 6337-6343.	1.9	87
3	Subnanometer-equivalent-oxide-thickness germanium p-metal-oxide-semiconductor field effect transistors fabricated using molecular-beam-deposited high-k/metal gate stack. Applied Physics Letters, 2006, 88, 132107.	3.2	71
4	Nanoindentation studies of multilayer amorphous carbon films. Carbon, 2004, 42, 1133-1136.	10.7	61
5	Germanium-induced stabilization of a very high-k zirconia phase in ZrO ₂ /GeO ₂ gate stacks. Applied Physics Letters, 2008, 93, 082904.	3.2	59
6	Very high-k ZrO ₂ with La ₂ O ₃ (LaGeOx) passivating interfacial layers on germanium substrates. Applied Physics Letters, 2008, 93, .	3.2	55
7	Joining of ceramic matrix composites to high temperature ceramics for thermal protection systems. Journal of the European Ceramic Society, 2016, 36, 443-449.	5.6	55
8	Electron energy band alignment at interfaces of (100)Ge with rare-earth oxide insulators. Applied Physics Letters, 2006, 88, 132111.	3.2	53
9	The role of La surface chemistry in the passivation of Ge. Applied Physics Letters, 2010, 96, .	3.2	51
10	Germanium MOSFETs With $\text{HfO}_2/\text{HfO}_2/\text{TiN}$ Gate Stacks. IEEE Transactions on Electron Devices, 2007, 54, 1425-1430.	3.2	37
11	Stabilization of very high-k tetragonal phase in Ge-doped ZrO ₂ films grown by atomic oxygen beam deposition. Journal of Applied Physics, 2009, 106, .	2.3	37
12	Epitaxial germanium-on-insulator grown on (001) Si. Microelectronic Engineering, 2007, 84, 2328-2331.	2.5	36
13	Homogeneous and amorphous sputtered sp ³ -bonded BN films at RT: a stress, spectroscopic ellipsometry and XPS study. Diamond and Related Materials, 2003, 12, 1151-1156.	4.0	34
14	Comprehensive study on the properties of multilayered amorphous carbon films. Diamond and Related Materials, 2000, 9, 756-760.	4.0	32
15	A quantitative study of the nano-scratch behavior of boron and carbon nitride films. Diamond and Related Materials, 2003, 12, 1088-1092.	4.0	29
16	Structural and optical properties of the recently synthesized (Zr _{3-x} Ti _x)AlC ₂ MAX phases. Journal of Materials Science: Materials in Electronics, 2017, 28, 3386-3393.	2.2	29
17	Germanium metal-insulator-semiconductor capacitors with rare earth La ₂ O ₃ gate dielectric. Microelectronic Engineering, 2007, 84, 2324-2327.	2.5	28
18	Stabilization of a very high-k tetragonal ZrO ₂ phase by direct doping with germanium. Microelectronic Engineering, 2009, 86, 1626-1628.	2.5	27

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19	A study on the bonding structure and mechanical properties of magnetron sputtered CN _x thin films. <i>Diamond and Related Materials</i> , 2001, 10, 1179-1184.	4.0	24
20	Variation of nitrogen incorporation and bonding configuration of carbon nitride films studied by X-ray photoelectron spectroscopy (XPS) and Fourier transform infrared (FT-IR) spectroscopic ellipsometry. <i>Diamond and Related Materials</i> , 2002, 11, 1183-1187.	4.0	23
21	Raman and photoluminescence study of magnetron sputtered amorphous carbon films. <i>Thin Solid Films</i> , 2002, 414, 18-24.	1.9	23
22	Total Dose Response of Ge MOS Capacitors With HfO ₂ /Dy ₂ O ₃ Gate Stacks. <i>IEEE Transactions on Nuclear Science</i> , 2007, 54, 971-974.	2.0	22
23	Germanium FETs and capacitors with rare earth CeO ₂ /HfO ₂ gates. <i>Solid-State Electronics</i> , 2007, 51, 1508-1514.	1.5	22
24	Chemical stability of lanthanum germanate passivating layer on Ge upon high-k deposition: A photoemission study on the role of La in the interface chemistry. <i>Journal of Applied Physics</i> , 2010, 108, .	2.3	20
25	Diffusion and Dopant Activation in Germanium: Insights from Recent Experimental and Theoretical Results. <i>Applied Sciences (Switzerland)</i> , 2019, 9, 2454.	2.6	20
26	Structural, electrical, and low-frequency-noise properties of amorphous-carbon-silicon heterojunctions. <i>Journal of Applied Physics</i> , 2001, 89, 2832-2838.	2.3	18
27	On the properties and functionality of ultra-thin diamond related protective coatings used in optical systems. <i>Sensors and Actuators A: Physical</i> , 2002, 99, 35-40.	4.2	18
28	Microstructure and its effect on the conductivity of magnetron sputtered carbon thin films. <i>Journal of Applied Physics</i> , 2001, 89, 7954-7959.	2.3	17
29	Post deposition annealing studies of lanthanum aluminate and ceria high-k dielectrics on germanium. <i>Microelectronics Reliability</i> , 2007, 47, 532-535.	1.8	16
30	Toward Defect Engineering Strategies to Optimize Energy and Electronic Materials. <i>Applied Sciences (Switzerland)</i> , 2017, 7, 674.	2.6	16
31	Noise characterization of sputtered amorphous carbon films. <i>Journal of Applied Physics</i> , 2000, 88, 5482-5484.	2.3	15
32	Electrical Properties of Atomic-Beam Deposited GeO _{1-x} N _x •HfO ₂ Gate Stacks on Ge. <i>Journal of the Electrochemical Society</i> , 2006, 153, G1112.	2.9	15
33	Magnetron sputtered carbon nitride: composition and chemical bonding of as-grown and post-annealed films studied with real-time and in situ diagnostic techniques. <i>Surface and Coatings Technology</i> , 2000, 125, 289-294.	4.9	14
34	Spectroscopic ellipsometry studies on BN films from IR to vacuum UV energy region. <i>Diamond and Related Materials</i> , 2002, 11, 1281-1285.	4.0	14
35	High-field transport and noise properties of sputter-deposited amorphous carbon-silicon heterojunctions. <i>Semiconductor Science and Technology</i> , 2002, 17, 662-667.	2.1	12
36	Lanthanum germanate as dielectric for scaled Germanium metal-oxide-semiconductor devices. <i>Microelectron Engineering</i> , 2009, 86, 1635-1637.	2.5	12

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37	Defect Process, Dopant Behaviour and Li Ion Mobility in the Li ₂ MnO ₃ Cathode Material. <i>Energies</i> , 2019, 12, 1329.	3.2	12
38	Magnetic skyrmion manipulation in CrTe ₂ /WTe ₂ 2D van der Waals heterostructure. <i>Applied Physics Letters</i> , 2022, 120, .	3.2	12
39	Mechanical performance and growth characteristics of boron nitride films with respect to their optical, compositional properties and density. <i>Surface and Coatings Technology</i> , 2002, 151-152, 155-159.	4.9	11
40	Copper diffusion in germanium: connecting point defect parameters with bulk properties. <i>Journal of Materials Science: Materials in Electronics</i> , 2015, 26, 2693-2696.	2.2	10
41	Electrical characterization of TiN/a-C/Si devices grown by magnetron sputtering at room temperature. <i>Applied Physics Letters</i> , 2001, 78, 1682-1684.	3.2	9
42	Current Challenges in Ge MOS Technology. <i>ECS Transactions</i> , 2006, 3, 371-384.	0.6	9
43	Metal-oxide-semiconductor devices on p-type Ge with La ₂ O ₃ and ZrO ₂ /La ₂ O ₃ as gate dielectric and the effect of postmetallization anneal. <i>Journal of Vacuum Science & Technology B</i> , 2009, 27, 246.	1.3	9
44	Atomistic Simulations of the Defect Chemistry and Self-Diffusion of Li-ion in LiAlO ₂ . <i>Energies</i> , 2019, 12, 2895.	3.2	9
45	Type-III Dirac fermions in Hf _x Zr _{1-x} Te ₂ topological semimetal candidate. <i>Journal of Applied Physics</i> , 2021, 129, .	2.3	9
46	The effect of Se and Se/Al passivation on the oxidation of Ge. <i>Microelectronic Engineering</i> , 2011, 88, 407-410.	2.5	8
47	The effects of interface and bulk defects on the electrical performance of amorphous carbon/silicon heterojunctions. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2002, 91-92, 379-383.	3.6	7
48	Tin diffusion in germanium: a thermodynamic approach. <i>Journal of Materials Science: Materials in Electronics</i> , 2017, 28, 9936-9940.	2.2	5
49	(Invited) Ge Surfaces and Its Passivation by Rare Earth Lanthanum Germanate Dielectric. <i>ECS Transactions</i> , 2010, 33, 433-446.	0.6	4
50	Self-Diffusion in Perovskite and Perovskite Related Oxides: Insights from Modelling. <i>Applied Sciences (Switzerland)</i> , 2020, 10, 2286.	2.6	4
51	Electrical properties of magnetron sputtered amorphous carbon films with sequential sp ³ -rich/sp ² -rich layered structure. <i>Applied Physics Letters</i> , 2001, 79, 3269-3271.	3.2	3
52	X-ray diffuse scattering investigation of thin films. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2003, 102, 25-29.	3.6	3
53	Characterization of Atomic-Beam Deposited GeO _{1-x} N _x /HfO ₂ Stacks on Ge. <i>ECS Transactions</i> , 2006, 1, 9-16.	0.6	3
54	Gate Dielectrics for High Mobility Semiconductors. <i>ECS Transactions</i> , 2008, 16, 295-306.	0.6	3

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55	Different nanostructures identified in boron nitride thin films grown on Si (100) by rf magnetron sputtering. <i>Diamond and Related Materials</i> , 2009, 18, 6-12.	4.0	3
56	Gold and silver diffusion in germanium: a thermodynamic approach. <i>Journal of Materials Science: Materials in Electronics</i> , 2017, 28, 1966-1970.	2.2	3
57	Effects of non-depositing energetic species during the growth of boron nitride and amorphous carbon thin films by sputter deposition. <i>Surface and Coatings Technology</i> , 2004, 180-181, 387-391.	4.9	2
58	Modelling the Defect Processes of Materials for Energy Applications. <i>Applied Sciences (Switzerland)</i> , 2022, 12, 9872.	2.6	2
59	Impact of La_2O_3 Thickness on $\text{HfO}_2/\text{La}_2\text{O}_3/\text{Ge}$ capacitors and p-channel MOSFETs. , 2009, , .		1
60	Very High-k Tetragonal ZrO_2 on Ge with GeO_2 Passivating Interfacial Layer. <i>ECS Transactions</i> , 2008, 16, 767-772.	0.6	1
61	Chalcogen Doping in SnO_2 : A DFT Investigation of Optical and Electronic Properties for Enhanced Photocatalytic Applications. <i>Materials</i> , 2024, 17, 3910.	3.0	0